

BC817 / BC818

NPN Silicon Epitaxial Planar Transistors

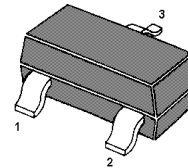
for switching, AF driver and amplifier application,

These transistors are subdivided into three groups

-16, -25, -40 according to their current gain.

As complementary types, the PNP transistors

BC807 and BC808 are recommended.



1. Base 2. Emitter 3. Collector
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	BC817 50	V
		BC818 30	
Collector Emitter Voltage	V_{CEO}	BC817 45	V
		BC818 25	
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	500	mA
Power Dissipation	P_{tot}	300	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at V _{CE} = 1 V, I _C = 100 mA	Current Gain Group -16 -25 -40	h _{FE}	100	-	250	-
		h _{FE}	160	-	400	-
		h _{FE}	250	-	600	-
at V _{CE} = 1 V, I _C = 500 mA		h _{FE}	40	-	-	-
Collector Base Cutoff Current at V _{CB} = 20 V	I _{CBO}	-	-	100	nA	
Emitter Base Cutoff Current at V _{EB} = 5 V	I _{EBO}	-	-	100	nA	
Collector Emitter Saturation Voltage at I _C = 500 mA, I _B = 50 mA	V _{CE(sat)}	-	-	0.7	V	
Base Emitter Voltage at I _C = 500 mA, V _{CE} = 1 V	V _{BE(on)}	-	-	1.2	V	
Transition Frequency at V _{CE} = 5 V, I _C = 10 mA, f = 50 MHz	f _T	100	-	-	MHz	
Collector Base Capacitance at V _{CB} = 10 V, f = 1 MHz	C _{ob}	-	5	-	pF	

